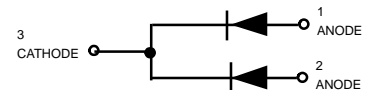
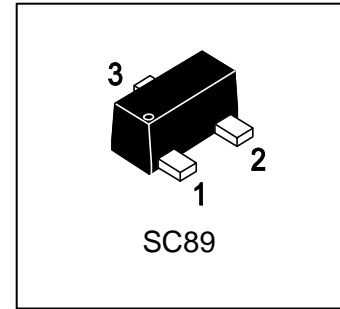


# LDAN222T1G

## S-LDAN222T1G

Common Cathode Silicon  
Dual Switching Diode



### 1. FEATURES

- Fast Trr
- Low CD
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

### 2. DEVICE MARKING AND RESISTOR VALUES

| Device     | Marking | Shipping        |
|------------|---------|-----------------|
| LDAN222T1G | N9      | 3000/Tape&Reel  |
| LDAN222T3G | N9      | 10000/Tape&Reel |

### 3. MAXIMUM RATINGS(Ta = 25°C)

| Parameter                          | Symbol | Limits | Unit |
|------------------------------------|--------|--------|------|
| Reverse Voltage                    | VR     | 100    | V    |
| Peak Reverse Voltage               | VRM    | 100    | V    |
| Forward Current                    | IF     | 100    | mA   |
| Peak Forward Current               | IFM    | 300    | mA   |
| Peak Forward Surge Current(Note 1) | IFSM   | 2      | A    |

### 4. THERMAL CHARACTERISTICS

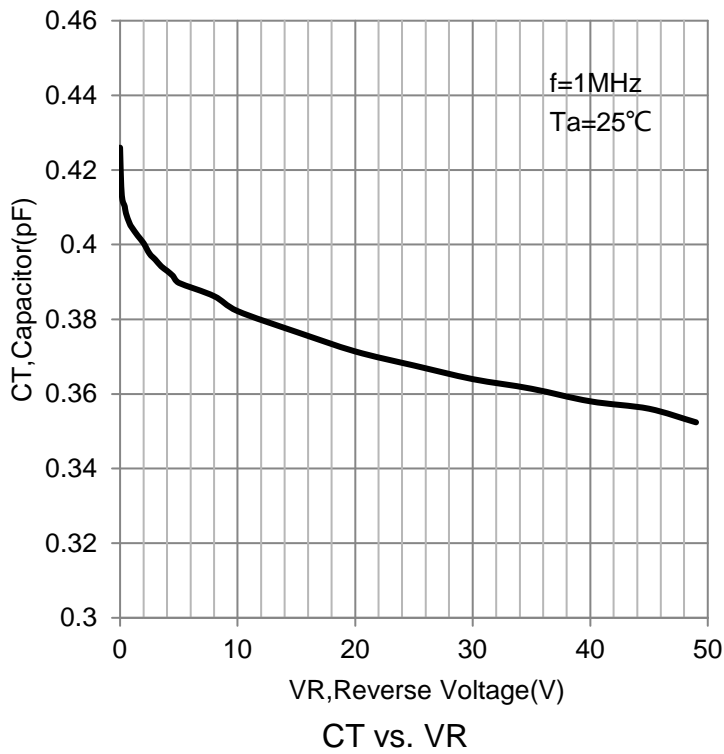
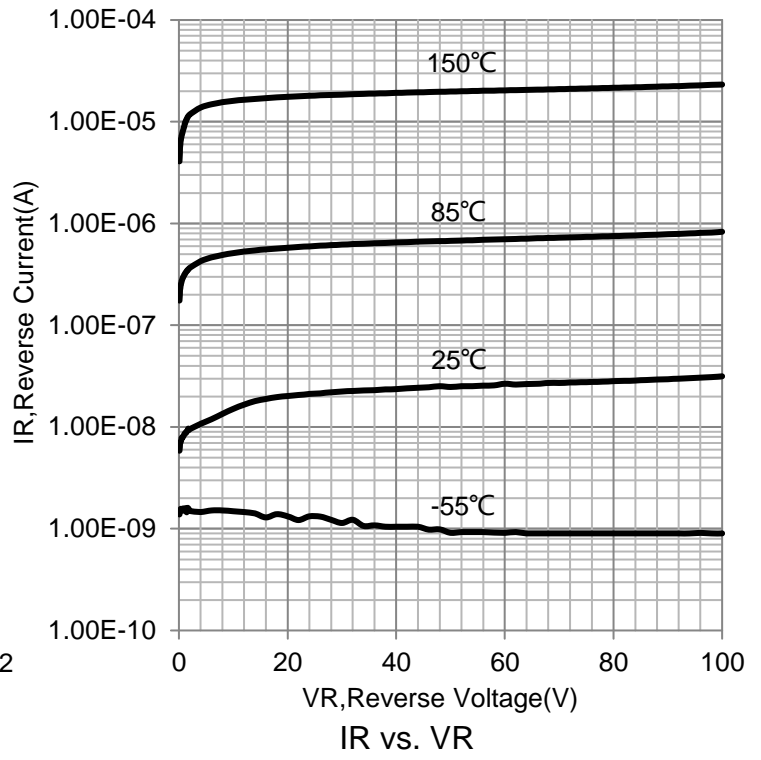
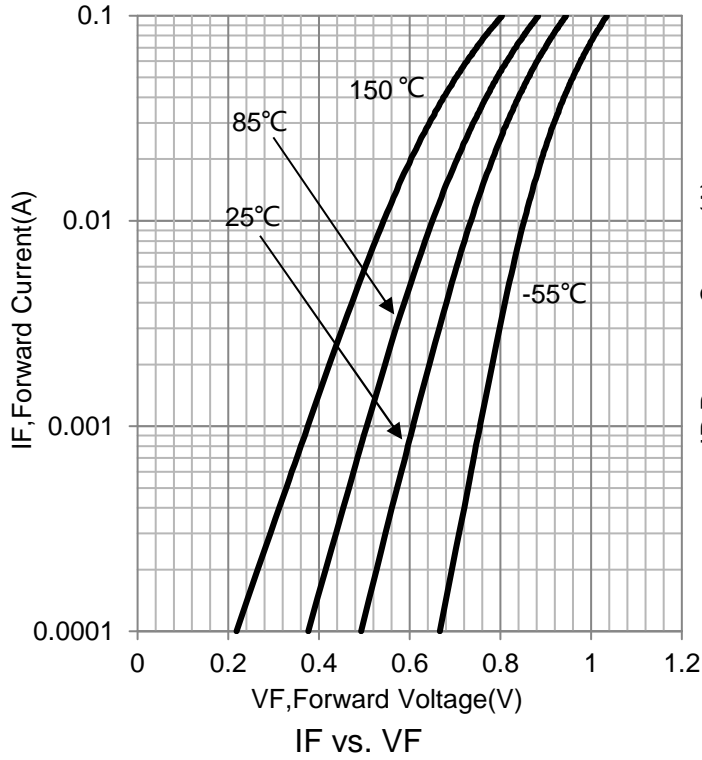
| Parameter                 | Symbol | Limits   | Unit |
|---------------------------|--------|----------|------|
| Power Dissipation         | PD     | 150      | mW   |
| Junction Temperature      | Tj     | 150      | °C   |
| Storage Temperature Range | Tstg   | -55~+150 | °C   |

1. t = 1 μS

**5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

| Characteristic   | Symbol | Min.   | Typ.   | Max.      | Unit |
|--|--------|--------|--------|-----------|------|
| Reverse Voltage Leakage Current<br>(VR = 70 V)<br>(VR = 100 V)               | IR     | -<br>- | -<br>- | 0.1<br>10 | μA   |
| Forward Voltage<br>(IF = 100 mA)   | VF     | -      | -      | 1.2       | V    |
| Reverse Breakdown Voltage<br>(IR = 100 μA )                                  | VR     | 100    | -      | -         | V    |
| Diode Capacitance<br>(VR = 6.0 V, f = 1.0 MHz)                               | CD     | -      | -      | 3.5       | pF   |
| Reverse Recovery Time<br>(IF = 5.0 mA, VR = 6.0 V, RL = 100 Ω, Irr = 0.1 IR) | Trr    | -      | -      | 4.0       | ns   |

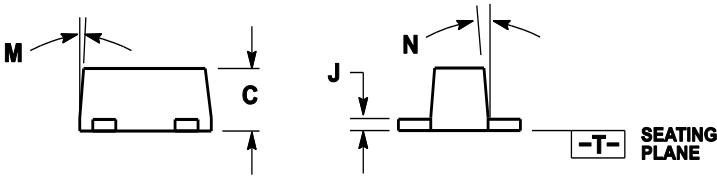
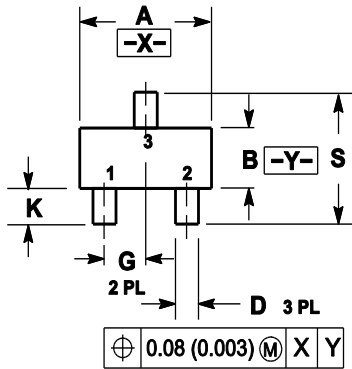
**6.ELECTRICAL CHARACTERISTICS CURVES**



### 7. OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



| DIM | MILLIMETERS |      |      | INCHES   |       |       |
|-----|-------------|------|------|----------|-------|-------|
|     | MIN         | NOM  | MAX  | MIN      | NOM   | MAX   |
| A   | 1.50        | 1.60 | 1.70 | 0.059    | 0.063 | 0.067 |
| B   | 0.75        | 0.85 | 0.95 | 0.030    | 0.034 | 0.040 |
| C   | 0.60        | 0.70 | 0.80 | 0.024    | 0.028 | 0.031 |
| D   | 0.23        | 0.28 | 0.33 | 0.009    | 0.011 | 0.013 |
| G   | 0.50BSC     |      |      | 0.020BSC |       |       |
| H   | 0.53REF     |      |      | 0.021REF |       |       |
| J   | 0.10        | 0.15 | 0.20 | 0.004    | 0.006 | 0.008 |
| K   | 0.30        | 0.40 | 0.50 | 0.012    | 0.016 | 0.02  |
| L   | 1.10REF     |      |      | 0.043REF |       |       |
| M   | ---         | ---  | 10°  | ---      | ---   | 10°   |
| N   | ---         | ---  | 10°  | ---      | ---   | 10°   |
| S   | 1.50        | 1.60 | 1.70 | 0.059    | 0.063 | 0.067 |

### 8. SOLDERING FOOTPRINT

